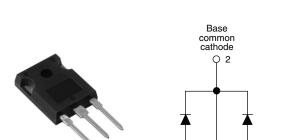


Vishay High Power Products

HEXFRED® Ultrafast Soft Recovery Diode, 2 x 8 A



Anode

Common cathode

TO-247AC

PRODUCT SUMMARY					
V _R per leg	1200 V				
V _F at 8 A at 25 °C	3.3 V				
I _{F(AV)}	2 x 8 A				
t _{rr} (typical)	28 ns				
T _J (maximum)	150 °C				
I _{RRM} (typical) per leg	4.5 A				

FEATURES

- · Ultrafast recovery
- · Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- · Specified at operating conditions
- · Designed and qualified for industrial level

BENEFITS

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION

HFA16PA120C is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A per leg continuous current, the HFA16PA120C is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA16PA120C is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Cathode to anode voltage	V_{R}		1200	V	
Maximum continuous forward current per leg	1_	T _C = 100 °C	8		
per device	- I _F		16	Α	
Single pulse forward current	I _{FSM}		130	A	
Maximum repetitive forward current	I _{FRM}		32		
Maximum newer dissination	P _D	T _C = 25 °C	73.5	W	
Maximum power dissipation		T _C = 100 °C	29		
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C	

HFA16PA120C

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ELECTRICAL SPECIFICATIONS PER LEG (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	Ι _R = 100 μΑ	1200	-	-	
Maximum forward voltage V _{FM}		I _F = 8.0 A	-	2.6	3.3	V
	V_{FM}	I _F = 16 A	-	3.4	4.3	
	I _F = 8.0 A, T _J = 125 °C	-	2.4	3.1		
Maximum reverse I _{RM}		V _R = V _R rated	-	0.31	10	
		T _J = 125 °C, V _R = 0.8 x V _R rated	-	135	1000	μΑ
Junction capacitance	C _T	V _R = 200 V	-	11	20	pF
Series inductance	L _S	Measured lead to lead 5 mm from package	-	8.0	-	nΗ

DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	28	-	
Reverse recovery time	t _{rr1}	T _J = 25 °C		-	63	95	ns
	t _{rr2}	T _J = 125 °C	I _F = 8.0 A dI _F /dt = 200 A/μs V _R = 200 V	-	106	160]
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.5	8.0	А
	I _{RRM2}	T _J = 125 °C		-	6.2	11	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	140	380	nC
	Q _{rr2}	T _J = 125 °C		-	335	880	
Peak rate of recovery current during $t_{\mbox{\scriptsize b}}$	dI _{(rec)M} /dt1	T _J = 25 °C		-	133	-	A/μs
	dI _{(rec)M} /dt2	T _J = 125 °C		-	85	-	Α/μδ

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R _{thJC}		-	-	1.7	
Thermal resistance, junction to ambient	R _{thJA}	R _{thJA} Typical socket mount		-	40	K/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.25	-	
Maight			-	6.0	-	g
Weight			-	0.21	-	OZ.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-247AC (JEDEC)	HFA16PA120C		•	

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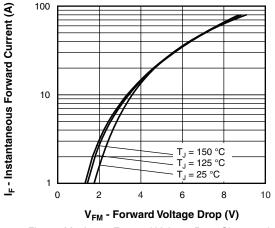


Fig. 1 - Maximum Forward Voltage Drop Characteristics

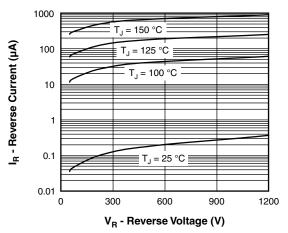


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

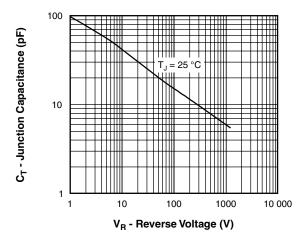


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

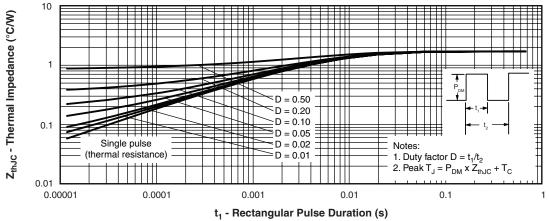


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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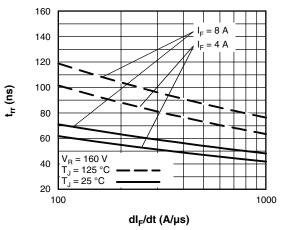


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt

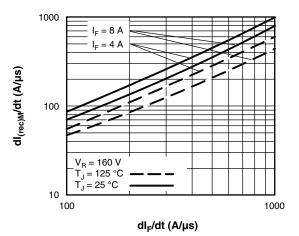


Fig. 7 - Typical Stored Charge vs. dI_F/dt

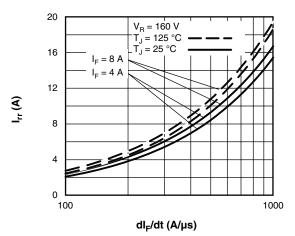


Fig. 6 - Typical Recovery Current vs. dl_F/dt

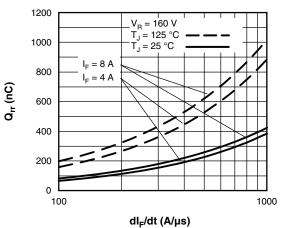


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt



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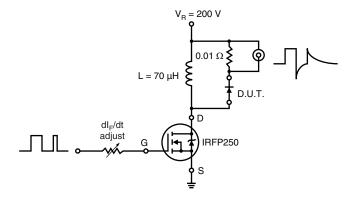
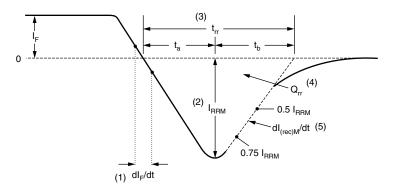


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- $\begin{array}{l} \text{(3) } \textbf{t}_{\text{rr}} \text{ reverse recovery time measured} \\ \text{from zero crossing point of negative} \\ \text{going I}_{\text{F}} \text{ to point where a line passing} \\ \text{through 0.75 I}_{\text{RRM}} \text{ and 0.50 I}_{\text{RRM}} \\ \text{extrapolated to zero current.} \end{array}$
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

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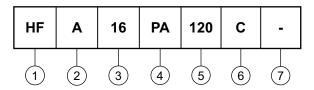
HEXFRED®



Ultrafast Soft Recovery Diode, 2 x 8 A

ORDERING INFORMATION TABLE

Device code



1 - HEXFRED® family

2 - Process designator: A = Subs. electron irradiated

B = Subs. platinum

3 - Current rating (16 = 16 A)

- Package outline (PA = TO-247, 3 pins)

Voltage rating (120 = 1200 V)

6 - Configuration (C = Center tap common cathode)

7 - • None = Standard production

• PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS					
Dimensions http://www.vishay.com/doc?95223					
Part marking information	http://www.vishay.com/doc?95226				

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